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FDS86106 N-Channel Power Trench[®] MOSFET 100 V, 3.4 A, 105 m Ω

Features

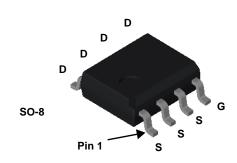
- Max $r_{DS(on)}$ = 105 m Ω at V_{GS} = 10 V, I_D = 3.4 A
- Max $r_{DS(on)}$ = 171 m Ω at V_{GS} = 6 V, I_D = 2.7 A
- High performance trench technology for extremely low r_{DS(on)}
- High power and current handling capability in a widely used surface mount package
- 100% UIL Tested
- RoHS Compliant

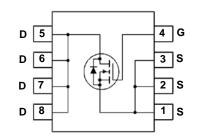


This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced Power Trench[®] process that has been optimized for $r_{DS(on)}$, switching performance and ruggedness.

Applications

- Synchronous Rectifier
- Primary Switch For Bridge Topology





MOSFET Maximum Ratings $T_A = 25 \degree C$ unless otherwise noted

Symbol	Parameter			Ratings	Units
V _{DS}	Drain to Source Voltage			100	V
V _{GS}	Gate to Source Voltage			±20	V
	Drain Current -Continuous			3.4	^
D	-Pulsed			15	A
E _{AS}	Single Pulse Avalanche Energy		(Note 3)	13	mJ
D	Power Dissipation	Г _А = 25 °С	(Note 1a)	5.0	W
PD	Power Dissipation T	A = 25 °C	(Note 1b)	2.5	vv
T _J , T _{STG}	Operating and Storage Junction Temperature Range	е		-55 to +150	°C

Thermal Characteristics

R_{\thetaJC}	Thermal Resistance, Junction to Case	(Note 1)	2.5	°C/W
R_{\thetaJA}	Thermal Resistance, Junction to Ambient	(Note 1a)	50	0/00

Package Marking and Ordering Information

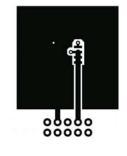
Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDS86106	FDS86106	SO-8	13 "	12 mm	2500 units

July 2011

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units	
Off Chara	octeristics						
BV _{DSS}	Drain to Source Breakdown Voltage	$I_{D} = 250 \ \mu A, \ V_{GS} = 0 \ V$	100		1	V	
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250 \ \mu$ A, referenced to 25 °C		67		mV/°C	
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 80 V, V _{GS} = 0 V			1	μΑ	
I _{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$			±100	nA	
On Chara	cteristics						
V _{GS(th)}	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \ \mu A$	2	2.9	4	V	
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250 \ \mu\text{A}$, referenced to 25 °C		-9		mV/°C	
j	Static Drain to Source On Resistance	V _{GS} = 10 V, I _D = 3.4 A		83	105		
r _{DS(on)}		$V_{GS} = 6 V, I_D = 2.7 A$		115	171	mΩ	
20(01)		$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 3.4 \text{ A}, \text{ T}_{J} = 125 \text{ °C}$		143	177	-	
9 _{FS}	Forward Transconductance	$V_{\rm DS} = 10$ V, $I_{\rm D} = 3.4$ A		6		S	
C _{iss} C _{oss} C _{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{DS} = 50 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1 MHz		156 47 2	208 62 3	pF pF pF	
C _{oss}					-		
R _q	Gate Resistance			0.9	-	Ω	
0	g Characteristics						
t _{d(on)}	Turn-On Delay Time			5	10	ns	
t _r	Rise Time	V _{DD} = 50 V, I _D = 3.4 A,		2	10	ns	
t _{d(off)}	Turn-Off Delay Time	V_{GS} = 10 V, R_{GEN} = 6 Ω		8	15	ns	
t _f	Fall Time			2	10	ns	
Q _{g(TOT)}	Total Gate Charge	$V_{GS} = 0 V$ to 10 V		3	4	nC	
⊲ g(101)	Total Gate Charge	$V_{GS} = 0 V \text{ to } 5 V V_{DD} = 50 V$		1.6	2.3	nC	
Q _{gs}	Total Gate Charge	I _D = 3.4 A		0.8		nC	
Q _{gd}	Gate to Drain "Miller" Charge			0.8		nC	
Drain-Sou	urce Diode Characteristics						
V	Source to Drain Diode, Eenward Valtage	$V_{GS} = 0 V, I_S = 3.4 A$ (Note 2)		0.86	1.3	V	
V _{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0 V, I_S = 2.1 A$ (Note 2)		0.83	1.2	v	
t	Reverse Recovery Time			34	54	ns	
t _{rr}		— I _F = 3.4 A, di/dt = 100 A/μs					

NOTES:

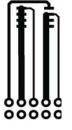
1. R_{0,A} is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. R_{0,JC} is guaranteed by design while R_{0CA} is determined by the user's board design.



2. Pulse Test: Pulse Width < 300 $\mu s,$ Duty cycle < 2.0 %.

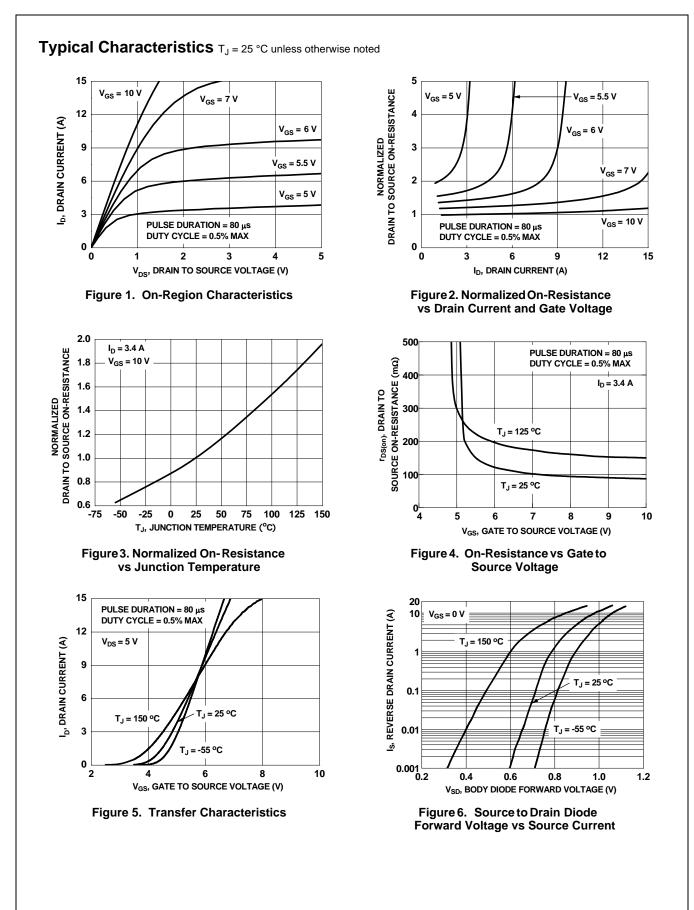
3. Starting T_J = 25 $^oC;$ N-ch: L = 3 mH, I_{AS} = 3 A, V_{DD} = 100 V, V_{GS} = 10 V.

a) 50 °C/W when mounted on a 1 in² pad of 2 oz copper.



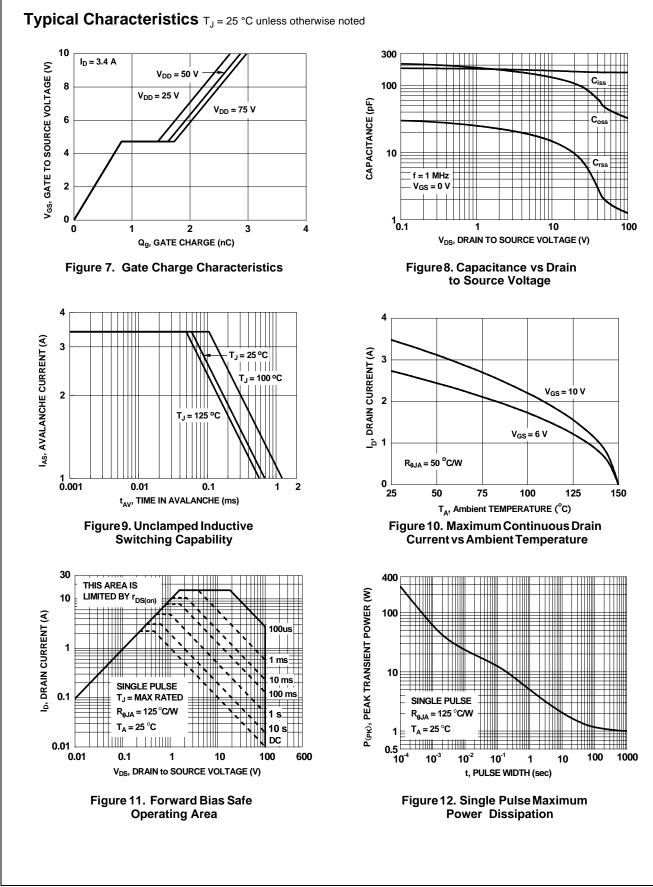
b) 125 °C/W when mounted on a minimum pad.

FDS86106 N-Channel Power Trench[®] MOSFET

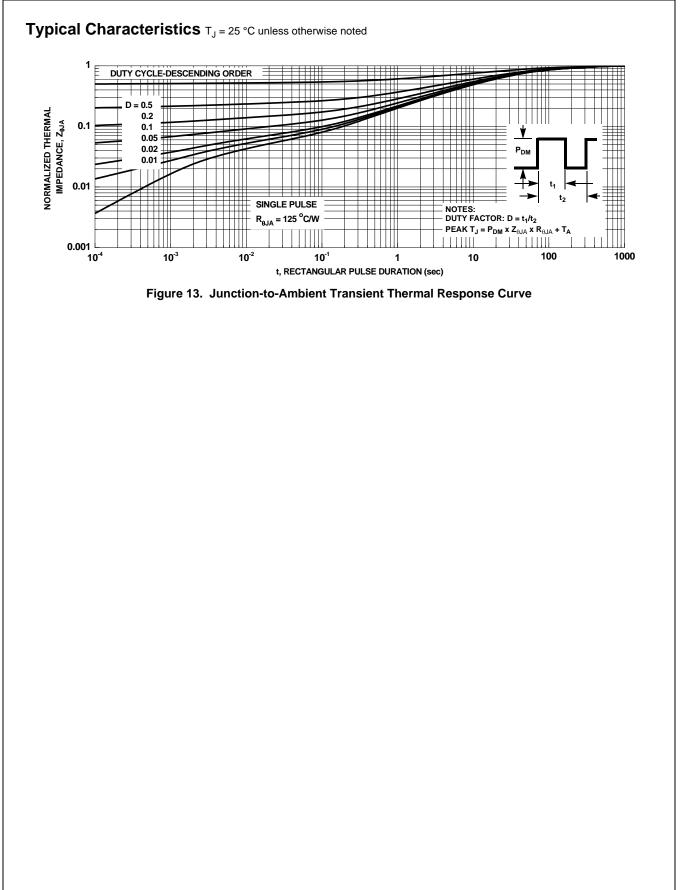


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